

**Patent 7,085,616**

**PATENT**

**IN UNITED STATES PATENT AND TRADEMARK OFFICE**

Patent No.: **7,085,616**

Docket No: **5017/ISM/CORE/MCVD/SB**

Issue Date: **August 1, 2006**

Patentee: **Chin, et al.**

Title

**ATOMIC LAYER DEPOSITION APPARATUS**

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**REQUEST FOR CERTIFICATION OF CORRECTION**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

It is requested that a Certificate of Correction be issued correcting printing errors appearing in the above-identified United States patent. A copy of the text of the Certificate in the suggested form is enclosed.

As the error is that of the Patent Office, it is believed that no fee is due. However, the Commissioner is authorized to charge any additional fees that may be due to Deposit Account No. 20-0782.

Issuance of the Certificate of Correction would neither expand nor contract the scope of the claims as properly allowed, and re-examination is not required.

Respectfully submitted,

Mar 8, 2007



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(Also Form PTO-1050)

## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,085,616

DATED : August 1, 2006

INVENTOR(S) : Chin et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 3, line 21, delete "processing such" and insert - - processing--such - -, therefor.

In column 3, line 60, below "pulsed flow." insert - - Thereafter as indicated in step 370 of FIG. 3, alternating monolayers of each deposition gas are chemisorbed onto the surface of the semiconductor wafer to form a material layer having a desired thickness thereon. Each monolayer is chemisorbed onto the surface of the semiconductor wafer as the wafer support is alternately moved between the two or more deposition regions through aperture 250. - -, as a new paragraph.

In column 4, line 10, in Claim 1, delete "a deposition" and insert - - a vacuum deposition - -, therefor.

In column 4, line 14, in Claim 1, after "support is" insert - - vertically - -.

In column 4, line 20, in Claim 3, delete "controls" and insert - - control - -, therefor.

In column 5, line 38, in Claim 15, after "support" delete "on" and insert - - to - -, therefor.

MAILING ADDRESS OF SENDER:

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